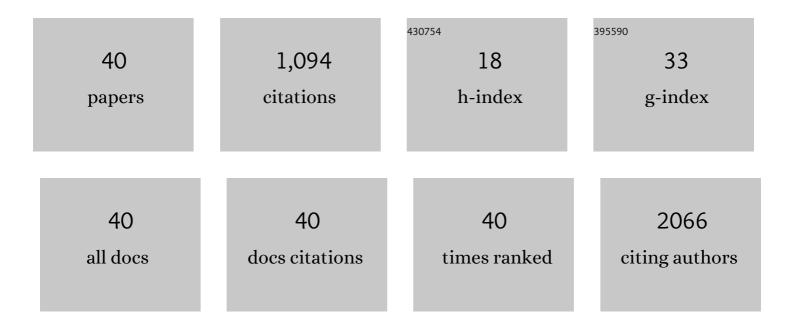
## Junhyeok Bang

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/6548535/publications.pdf Version: 2024-02-01



#	Article	IF	CITATIONS
1	Diffusion and thermal stability of hydrogen in ZnO. Applied Physics Letters, 2008, 92, . Deep electron traps and origin of <mml:math <br="" xmlns:mml="http://www.w3.org/1998/Math/MathML">display="inline"&gt;<mml:mi>p</mml:mi></mml:math> -type conductivity in the earth-abundant solar-cell	1.5	122
2	material Cu <mml:math <br="" xmlns:mml="http://www.w3.org/1998/Math/MathML">display="inline"&gt;<mml:msub><mml:mrow /&gt;<mml:mn>2</mml:mn></mml:mrow </mml:msub></mml:math> ZnSnS <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"&gt;<mml:msub><mml:mrow< td=""><td>1.1</td><td>110</td></mml:mrow<></mml:msub></mml:math 	1.1	110
3	The role of collective motion in the ultrafast charge transfer in van der Waals heterostructures. Nature Communications, 2016, 7, 11504.	5.8	103
4	Atomic and electronic structures of single-layer FeSe on SrTiO <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"&gt;<mml:msub><mml:mrow /&gt;<mml:mn>3</mml:mn></mml:mrow </mml:msub>(001): The role of oxygen deficiency. Physical Review B, 2013, 87, .</mml:math 	1.1	86
5	Modification of Defect Structures in Graphene by Electron Irradiation: Ab Initio Molecular Dynamics Simulations. Journal of Physical Chemistry C, 2012, 116, 16070-16079.	1.5	61
6	Electron-Rich Driven Electrochemical Solid-State Amorphization in Li–Si Alloys. Nano Letters, 2013, 13, 4511-4516.	4.5	51
7	Multivalency-Induced Band Gap Opening at MoS <sub>2</sub> Edges. Chemistry of Materials, 2015, 27, 3326-3331.	3.2	50
8	Localization and one-parameter scaling in hydrogenated graphene. Physical Review B, 2010, 81, .	1.1	45
9	Photoinduced Vacancy Ordering and Phase Transition in MoTe <sub>2</sub> . Nano Letters, 2019, 19, 3612-3617.	4.5	43
10	Directional Forces by Momentumless Excitation and Order-to-Order Transition in Peierls-Distorted Solids: The Case of GeTe. Physical Review Letters, 2018, 120, 185701.	2.9	38
11	Understanding the presence of vacancy clusters in ZnO from a kinetic perspective. Applied Physics Letters, 2014, 104, 252101.	1.5	34
12	Regulating energy transfer of excited carriers and the case for excitation-induced hydrogen dissociation on hydrogenated graphene. Proceedings of the National Academy of Sciences of the United States of America, 2013, 110, 908-911.	3.3	32
13	Time-dependent density-functional theory molecular-dynamics study on amorphization of Sc-Sb-Te alloy under optical excitation. Npj Computational Materials, 2020, 6, .	3.5	32
14	Carrier-Multiplication-Induced Structural Change during Ultrafast Carrier Relaxation and Nonthermal Phase Transition in Semiconductors. Physical Review Letters, 2016, 117, 126402.	2.9	29
15	Molecular doping of ZnO by ammonia: a possible shallow acceptor. Journal of Materials Chemistry C, 2015, 3, 339-344.	2.7	28
16	Triangular Black Phosphorus Atomic Layers by Liquid Exfoliation. Scientific Reports, 2016, 6, 23736.	1.6	28
17	Electronic structure and transport properties of hydrogenated graphene and graphene nanoribbons. New Journal of Physics, 2010, 12, 125005.	1.2	23
18	Atomic Structure and Diffusion of Hydrogen in ZnO. Journal of the Korean Physical Society, 2009, 55, 98-102.	0.3	20

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#	Article	IF	CITATIONS
19	Difficulty in predicting shallow defects with hybrid functionals: Implication of the long-range exchange interaction. Physical Review B, 2013, 88, .	1.1	18
20	Phase diagram of graphene nanoribbons and band-gap bifurcation of Dirac fermions under quantum confinement. Physical Review B, 2012, 85, .	1.1	16
21	Ab initio study of boron segregation and deactivation at Si/SiO2 interface. Microelectronic Engineering, 2012, 89, 120-123.	1.1	16
22	Phase Transition in a Memristive Suspended MoS <sub>2</sub> Monolayer Probed by Opto- and Electro-Mechanics. ACS Nano, 2020, 14, 13611-13618.	7.3	13
23	Carrier Dynamics and Transfer across the CdS/MoS <sub>2</sub> Interface upon Optical Excitation. Journal of Physical Chemistry Letters, 2020, 11, 6544-6550.	2.1	13
24	Suppression of nonradiative recombination in ionic insulators by defects: Role of fast electron trapping in Tl-doped CsI. Physical Review B, 2013, 87, .	1.1	12
25	Carrier-induced transient defect mechanism for non-radiative recombination in InGaN light-emitting devices. Scientific Reports, 2016, 6, 24404.	1.6	10
26	Optical subpicosecond nonvolatile switching and electron-phonon coupling in ferroelectric materials. Physical Review B, 2020, 102, .	1.1	9
27	Giant lattice expansion by quantum stress and universal atomic forces in semiconductors under instant ultrafast laser excitation. Physical Chemistry Chemical Physics, 2017, 19, 24735-24741.	1.3	7
28	Strain-induced indium clustering in non-polar a-plane InGaN quantum wells. Acta Materialia, 2018, 145, 109-122.	3.8	7
29	Phonon-Enabled Carrier Transport of Localized States at Non-Polar Semiconductor Surfaces: A First-Principles-Based Prediction. Journal of Physical Chemistry Letters, 2016, 7, 3548-3553.	2.1	6
30	Fully Bottomâ€Up Wasteâ€Free Growth of Ultrathin Silicon Wafer via Selfâ€Releasing Seed Layer. Advanced Materials, 2021, 33, e2103708.	11.1	6
31	Robust ferromagnetism in hydrogenated graphene mediated by spin-polarized pseudospin. Scientific Reports, 2018, 8, 13940.	1.6	5
32	Dynamic defect as nonradiative recombination center in semiconductors. Physical Review B, 2019, 100, .	1.1	5
33	Nonlocal effect of excited carriers on the bond strength of carbazole-based OLED host materials. Physical Review Materials, 2020, 4, .	0.9	4
34	Microscopic Origin for Electrically Benign Small-angle Grain Boundaries in Low-cost Semiconductors. Materials Research Letters, 2014, 2, 51-56.	4.1	3
35	Substrate effect on hydrogen evolution reaction in two-dimensional Mo2C monolayers. Scientific Reports, 2022, 12, 6076.	1.6	3
36	Nonequilibrium Charge-Density-Wave Melting in 1 <i>T</i> -TaS <sub>2</sub> Triggered by Electronic Excitation: A Real-Time Time-Dependent Density Functional Theory Study. Journal of Physical Chemistry Letters, 2022, 13, 5711-5718.	2.1	3

#	Article	IF	CITATIONS
37	Doping-induced antiferromagnetic bicollinear insulating state and superconducting temperature of monolayer FeSe systems. Physical Review B, 2018, 98, .	1.1	2
38	Subband-enhanced carrier multiplication in graphene nanoribbons. Physical Review B, 2021, 104, .	1.1	1
39	Electronic Structure of O-vacancy in High-k Dielectrics and Oxide Semiconductors. Materials Research Society Symposia Proceedings, 2011, 1370, 3.	0.1	0

Fully Bottom $\hat{a} \in Up$  Waste $\hat{a} \in Free$  Growth of Ultrathin Silicon Wafer via Self $\hat{a} \in Releasing$  Seed Layer (Adv.) Tj ETQq0 0.0 rgBT /Overlock 10